# EMB2 / UMB2N / IMB2A

PNP -100mA -50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Tr1 and Tr2
V <sub>CC</sub>	-50V
I <sub>C(MAX.)</sub>	-100mA
R <sub>1</sub>	47kΩ
$R_2$	47kΩ

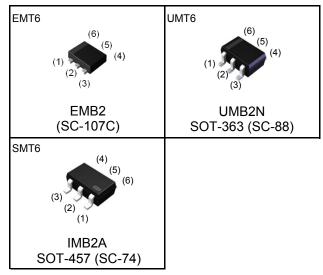
#### Features

- 1) Built-In Biasing Resistors,  $R_1 = R_2 = 47k\Omega$ .
- 2) Two DTA144E chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

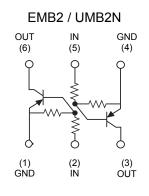
#### Application

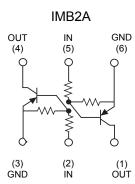
Inverter circuit, Interface circuit, Driver circuit

#### Outline



#### ●Inner circuit





Datasheet

#### Packaging specifications

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Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMB2	EMT6	1616	T2R	180	8	8,000	B2
UMB2N	UMT6	2021	TN	180	8	3,000	B2
IMB2A	SMT6	2928	T110	180	8	3,000	B2

## ● Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parar	neter	Symbol	Values	Unit
Supply voltage		V <sub>CC</sub>	-50	V
Input voltage		V <sub>IN</sub>	-40 to +10	V
Output current		Io	-30	mA
Collector current		I <sub>C(MAX.)</sub> *1	-100	mA
Power dissipation EMB3 / UMB3N		D *2	150 (Total) <sup>*3</sup>	mW
IMB3A		P <sub>D</sub> <sup>-2</sup>	300 (Total) <sup>*4</sup>	mW
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperat	ture	T <sub>stg</sub>	−55 to +150	°C

## ●Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	$V_{I(off)}$	$V_{CC} = -5V, I_{O} = -100 \mu A$	ı	ı	-0.5	V
	$V_{I(on)}$	$V_0 = -0.3V, I_0 = -2mA$	-3.0	-	-	V
Output voltage	$V_{O(on)}$	$I_0 / I_1 = -10 \text{mA} / -0.5 \text{mA}$	-	-0.1	-0.3	V
Input current	$I_1$	V <sub>I</sub> = -5V	1	1	-0.18	mA
Output current	I <sub>O(off)</sub>	$V_{CC} = -50V, V_1 = 0V$	-	-	-0.5	μΑ
DC current gain	Gı	$V_{\rm O} = -5V, I_{\rm O} = -5mA$	68	-	-	-
Input resistance	R <sub>1</sub>	-	32.9	47	61.1	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	-	0.8	1	1.2	-
Transition frequency	f <sub>T</sub> *1	$V_{CE} = -10V, I_{E} = 5mA,$ f = 100MHz	-	250	1	MHz

<sup>\*1</sup> Characteristics of built-in transistor

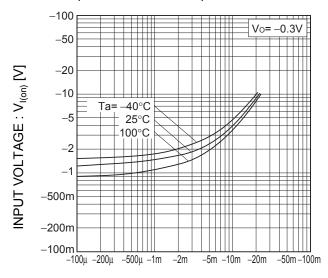
<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 120</sup>mW per element must not be exceeded.

<sup>\*4 200</sup>mW per element must not be exceeded.

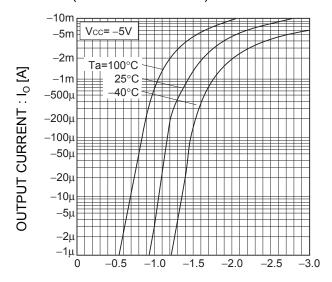
#### ●Electrical characteristic curves(Ta = 25°C)

Fig.1 Input voltage vs. output current (ON characteristics)



OUTPUT CURRENT : Io [A]

Fig.2 Output current vs. input voltage (OFF characteristics)



INPUT VOLTAGE: V<sub>I(off)</sub>[V]

Fig.3 Output current vs. output voltage

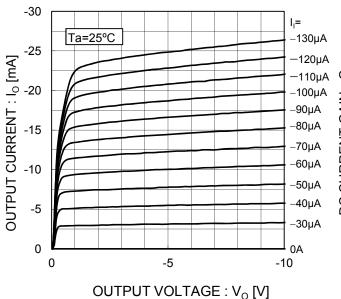
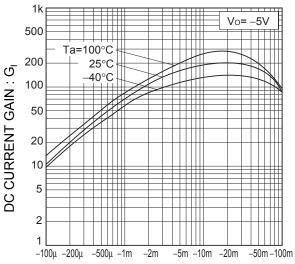


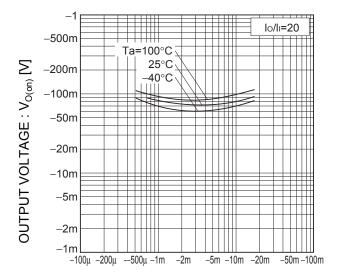
Fig.4 DC current gain vs. output current



OUTPUT CURRENT : Io [A]

# ●Electrical characteristic curves(Ta = 25°C)

Fig.5 Output voltage vs. output current

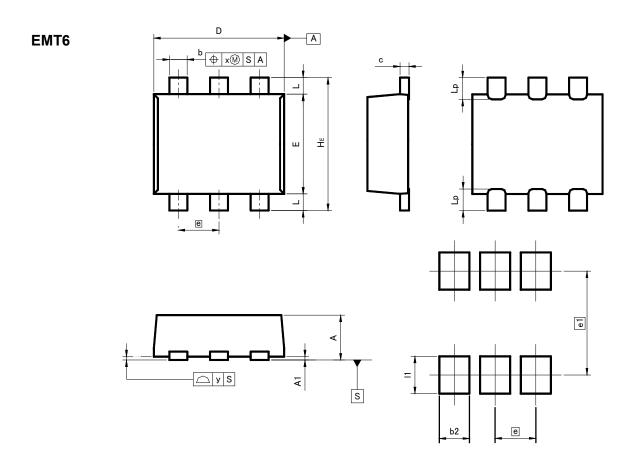


OUTPUT CURRENT : I<sub>O</sub> [A]

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2014.10 - Rev.C

# ●Dimensions (Unit : mm)



## Patterm of terminal position areas

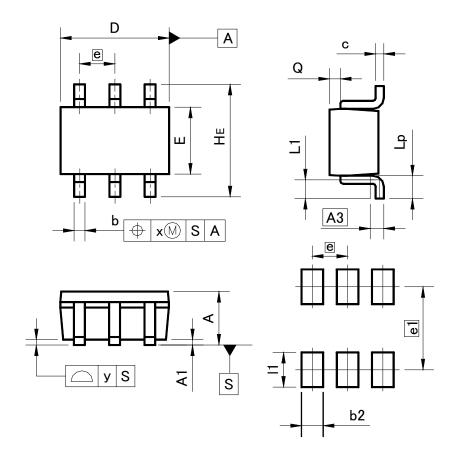
DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
Α	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
е	0.	50	0.02	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	_	0.35	-	0.014
х	_	0.10		0.004
У	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	_	0.37	_	0.015	
l1	_	0.45	_	0.018	

Dimension in mm/inches

# ●Dimensions (Unit : mm)

## UMT6



#### Patterm of terminal position areas

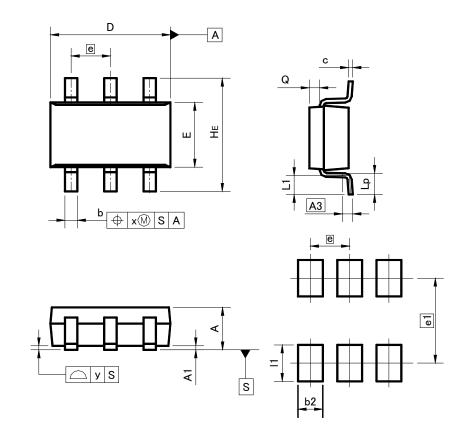
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	ı	0.039	
A1	0.00	0.10	0	0.004	
A3	0.2	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	-	0.004	
У	_	0.10	-	0.004	

DIM	MILIMETERS		INCHES		
DIM MIN		MAX	MIN	MAX	
e1	1.55		0.06		
b2	-	0.40	ı	0.016	
11	_	0.65	-	0.026	

Dimension in mm/inches

# ●Dimensions (Unit : mm)

## SMT6



## Patterm of terminal position areas

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.3	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
Е	1.50	1.80	0.059	0.071	
е	0.9	0.95		04	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	1	0.024	
11	-	0.90	ı	0.035	

Dimension in mm/inches

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